

isc Silicon NPN Power Transistor

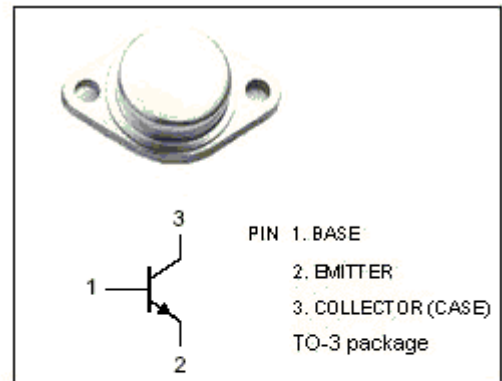
2SC2488

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 150V(\text{Min.})$
- Good Linearity of h_{FE}
- Wide Area of Safe Operation
- Complement to Type 2SA1064

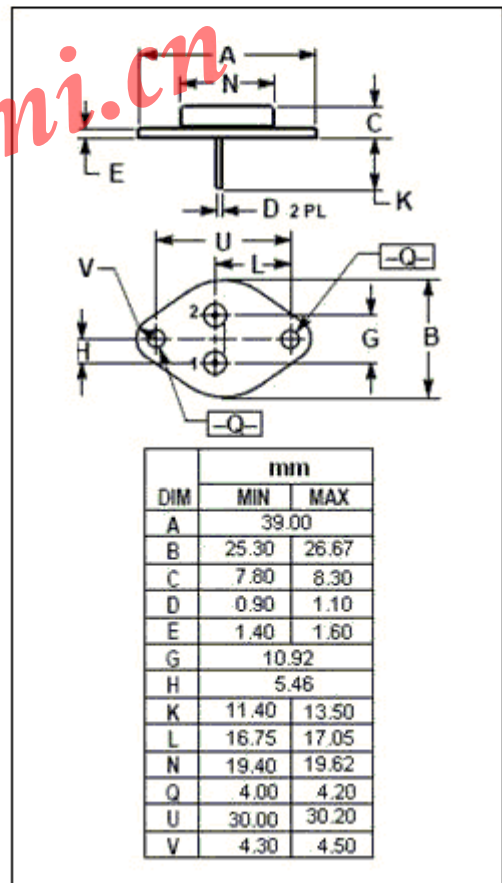
APPLICATIONS

- Designed for AF amplifier, high power amplifier applications.



ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	150	V
V_{CEO}	Collector-Emitter Voltage	150	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	8	A
I_{CM}	Collector Current-Peak	12	A
P_C	Collector Power Dissipation @ $T_c=25^{\circ}C$	100	W
T_j	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-65~150	$^{\circ}C$



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ELECTRICAL CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 100mA; I _B = 0	150			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 8A; I _B = 0.8A			2.0	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 8A; V _{CE} = 5V			2.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 70V; I _E = 0			1	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			2	mA
h _{FE-1}	DC Current Gain	I _C = 1A; V _{CE} = 5V	40		280	
h _{FE-2}	DC Current Gain	I _C = 8A; V _{CE} = 5V	20			
f _T	Current-Gain—Bandwidth Product	I _C = 0.5A; V _{CE} = 10V		50		MHz

◆ h_{FE-2} Classifications

R	Q	P	O
40-80	60-120	90-180	140-280